74LV74Dual D-type flip-flop with set and reset; positive-edge triggerRev. 3 - 9 September 2013Product data sheet

### 1. General description

The 74LV74 is a dual positive edge triggered, D-type flip-flop. It has individual data (nD) inputs, clock (nCP) inputs, set (nSD) and (nRD) inputs, and complementary nQ and nQ outputs.

The set and reset are asynchronous active LOW inputs that operate independently of the clock input. Information on the data input is transferred to the nQ output on the LOW-to-HIGH transition of the clock pulse. The nD inputs must be stable one set-up time prior to the LOW-to-HIGH clock transition, for predictable operation. Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.

## 2. Features and benefits

- Wide supply voltage range from 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Direct interface with TTL levels (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114-A exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

## 3. Ordering information

Ordering information

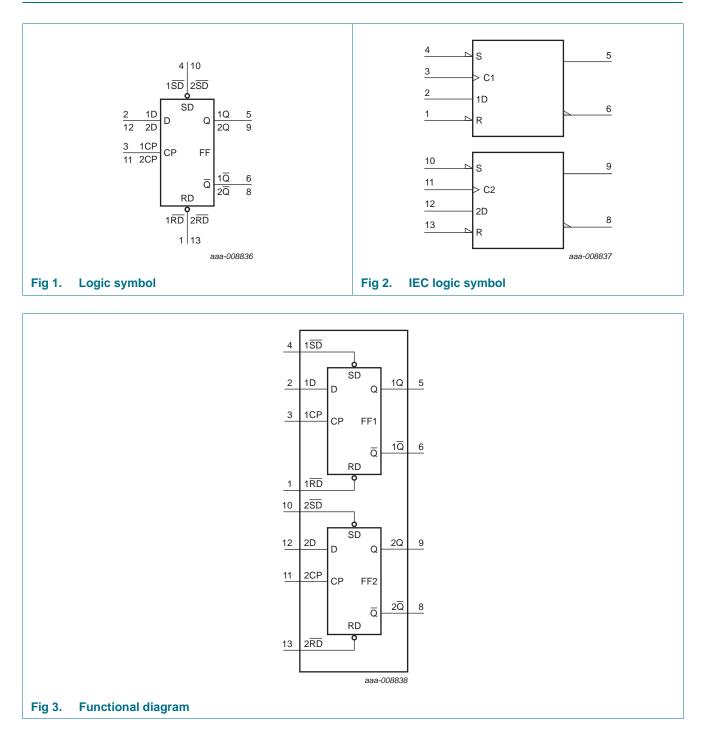
Table 1

Type number	Package									
	Temperature range	Name	Description	Version						
74LV74N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1						
74LV74D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1						
74LV74DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1						
74LV74PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1						

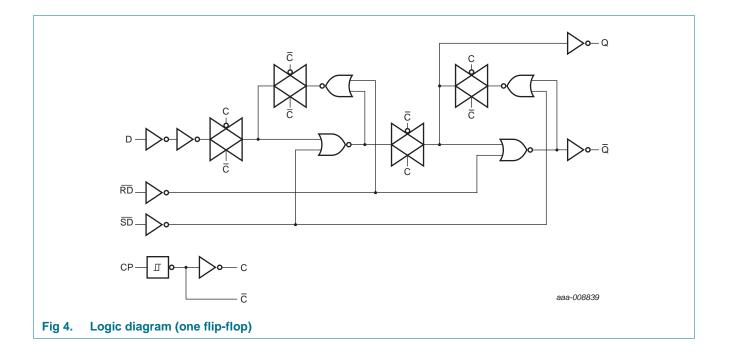
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#### Dual D-type flip-flop with set and reset; positive-edge trigger

# 4. Functional diagram

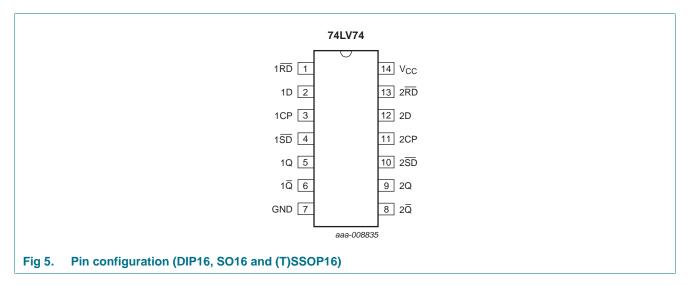


Dual D-type flip-flop with set and reset; positive-edge trigger



# 5. Pinning information

## 5.1 Pinning



# 5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
1RD	1	asynchronous reset-direct input (active-LOW)
1D	2	data inputs
1CP	3	clock input (LOW-to-HIGH), edge-triggered)
1SD	4	asynchronous set-direct input (active-LOW)
1Q	5	true flip-flop outputs
1 <mark>Q</mark>	6	complement flip-flop outputs
GND	7	ground (0 V)
2 <mark>Q</mark>	8	complement flip-flop outputs
2Q	9	true flip-flop outputs
2SD	10	asynchronous set-direct input (active-LOW)
2CP	11	clock input (LOW-to-HIGH), edge-triggered)
2D	12	data inputs
2RD	13	asynchronous reset-direct input (active-LOW)
V <sub>CC</sub>	14	supply voltage

# 6. Functional description

#### Table 3.Function table[1]

			Output	Output			
nSD	nRD	nCP	nD	nQ	nQ	Q <sub>n+1</sub>	nQ <sub>n+1</sub>
L	Н	x	Х	Н	L	-	-
Н	L	Х	Х	L	Н	-	-
L	L	Х	Х	Н	Н	-	-
Н	Н	$\uparrow$	L	-	-	L	Н
Н	Н	$\uparrow$	Н	-	-	Н	L

[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

 $\uparrow$  = LOW-to-HIGH clock transition;

 $Q_{n+1}$  = state after the next LOW-to-HIGH CP transition

# 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage		<u>[1]</u>	-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC}$ + 0.5 V		-	20	mA
VI	input voltage		<u>[1]</u>	-0.5	+7	V
Ι <sub>ΟΚ</sub>	output clamping current	$V_{\rm O} > V_{\rm CC}$ or $V_{\rm O} < 0$		-	±50	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±25	mA
I <sub>CC</sub>	supply current			-	±50	mA
I <sub>GND</sub>	ground current			-	±50	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C				
		DIP16 package	[	2] _	750	mW
		SO16 package	[	3] _	500	mW
		(T)SSOP16 package	[	4] _	400	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P<sub>tot</sub> derates linearly with 12 mW/K above 70 °C.

[3]  $P_{tot}$  derates linearly with 8 mW/K above 70 °C.

[4]  $P_{tot}$  derates linearly with 5.5 mW/K above 60 °C.

# 8. Recommended operating conditions

#### Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

0	10 /					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage <sup>[1]</sup>		1.0	3.3	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC}$ = 1.0 V to 2.0 V	0	-	500	ns/V
		$V_{CC}$ = 2.0 V to 2.7 V	0	-	200	ns/V
		$V_{CC}$ = 2.7 V to 3.6 V	0	-	100	ns/V
		$V_{CC}$ = 3.6 V to 5.5 V	0	-	50	ns/V

[1] LV is guaranteed to function down to  $V_{CC}$  = 1.0 V (input levels GND or  $V_{CC}$ ); DC characteristics are guaranteed from  $V_{CC}$  = 1.2 V to  $V_{CC}$  = 5.5 V.

# 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	–40 °C to	Uni	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
V <sub>IH</sub> HIGH-level		V <sub>CC</sub> = 1.2 V	0.9	-	-	0.9	-	V
	input voltage	$V_{CC}$ = 2.3 V to 2.7 V	1.4	-	-	1.4	-	V
		$V_{CC}$ = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		$V_{CC}$ = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	$0.7\times V_{CC}$	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 1.2 V	-	-	0.3	-	0.3	V
	input voltage	$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.6	-	0.6	V
		$V_{CC}$ = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		$V_{CC}$ = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	-	$0.3\times V_{CC}$	
Vон	HIGH-level	$V_I = V_{IH} \text{ or } V_{IL}; \ I_O = -100 \ \mu A$						
	output voltage	$V_{CC} = 1.2 V$	-	1.2		-		
		$V_{CC} = 2.0 V$	1.8	2.0	-	1.8	-	V
		$V_{CC} = 2.7 V$	2.5	2.7	-	2.5	-	V
		$V_{CC} = 3.0 V$	2.8	3.0	-	2.8	-	V
		$V_{CC} = 4.5 V$	4.3	4.5	-	4.3	-	V
		standard outputs: $V_I = V_{IH}$ or $V_{IL}$						
		$V_{CC}$ = 3.0 V; I <sub>O</sub> = -6 mA	2.40	2.82	-	2.20	-	V
		$V_{CC}$ = 4.5 V; I <sub>O</sub> = -12 mA	3.60	4.20	-	3.50	-	V
/ <sub>OL</sub>	LOW-level	$V_{I}$ = $V_{IH}$ or $V_{IL};I_{O}$ = 100 $\mu A$						
	output voltage	$V_{CC} = 1.2 V$	-	0	-	-	-	
		$V_{CC} = 2.0 V$	-	0	0.2		0.2	V
		$V_{CC} = 2.7 V$	-	0	0.2		0.2	V
		$V_{CC} = 3.0 V$	-	0	0.2		0.2	V
		$V_{CC} = 4.5 V$	-	0	0.2		0.2	V
		standard outputs: $V_I = V_{IH}$ or $V_{IL}$						
		$V_{CC} = 3.0 \text{ V}; I_{O} = 6 \text{ mA}$	-	0.25	0.40	-	0.50	V
		$V_{CC} = 4.5 \text{ V}; I_{O} = 12 \text{ mA}$	-	0.35	0.55	-	0.65	V
I	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	±1	-	±1	μA
сс	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 5.5$ V	-	-	20	-	80	μA
Alcc	additional supply current		-	-	500	-	850	μA
C <sub>I</sub>	input capacitance		-	3.5	-			pF

[1] Typical values are measured at  $T_{amb} = 25 \ ^{\circ}C$ .

# **10.** Dynamic characteristics

#### Table 7.Dynamic characteristics

GND (ground = 0 V): for test circuit, see Figure 8

Symbol	Parameter	Conditions		-40	) °C to +8	5 °C	–40 °C to	o +125 ℃	Unit
				Min	Typ[1]	Max	Min	Мах	
t <sub>pd</sub>	propagation	nCP to nQ, nQ; see <u>Figure 6</u>	[2]						
	delay	$V_{CC} = 1.2 V$		-	70	-	-	-	ns
		$V_{CC} = 2.0 V$		-	24	44	-	56	ns
		$V_{CC} = 2.7 V$		-	18	28	-	41	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[3]	-	13	26	-	33	ns
		$V_{CC} = 3.3 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[4]	-	9.5	17	-	23	ns
		$n\overline{SD}$ to $nQ$ , $n\overline{Q}$ ; see <u>Figure 7</u>							
		$V_{CC} = 1.2 V$		-	90	-	-	-	ns
		$V_{CC} = 2.0 V$		-	31	46	-	58	ns
		$V_{CC} = 2.7 V$		-	23	34	-	43	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[3]	-	17	27	-	34	ns
		$V_{CC} = 3.3 \text{ V}; C_L = 15 \text{ pF}$		-	14	-	-	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[4]	-	12	19	-	24	ns
		$n\overline{RD}$ to $nQ$ , $n\overline{Q}$ ; see Figure 7							
		$V_{CC} = 1.2 V$		-	90	-	-	-	ns
		$V_{CC} = 2.0 V$		-	31	46	-	58	ns
		$V_{CC} = 2.7 V$		-	23	34	-	43	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[3]	-	17	27	-	34	ns
		$V_{CC} = 3.3 \text{ V}; C_L = 15 \text{ pF}$		-	14	-	-	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[4]	-	12	19	-	24	ns
W	pulse width	nCP input HIGH to LOW; see <mark>Figure 6</mark>							
		$V_{CC} = 2.0 V$		34	10	-	41	-	ns
		$V_{CC} = 2.7 V$		25	8	-	30	-	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[3]	20	7	-	24	-	ns
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	[4]	15	6	-	18	-	ns
		nSD or nRD pulse width LOW; see Figure 7							
		$V_{CC} = 2.0 V$		34	10	-	41	-	ns
		$V_{CC} = 2.7 V$		25	8	-	30	-	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	[3]	20	7	-	24	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[4]	15	6	-	18	-	ns

#### Dual D-type flip-flop with set and reset; positive-edge trigger

Symbol	Parameter	Conditions		-40	) °C to +8	5 °C	_40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t <sub>rec</sub>	recovery time	nRD; see Figure 7	ľ					•	
		V <sub>CC</sub> = 1.2 V		-	5	-	-	-	ns
		$V_{CC} = 2.0 V$		14	2	-	15	-	ns
		$V_{CC} = 2.7 V$		10	1	-	11	-	ns
		$V_{CC}$ = 3.0 V to 3.6 V	<u>[3]</u>	8	1	-	9	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[4]	6	1	-	7	-	ns
t <sub>su</sub>	set-up time	nD to nCP; see Figure 6							
		V <sub>CC</sub> = 1.2 V		-	10	-	-	-	ns
		$V_{CC} = 2.0 V$		22	4	-	26	-	ns
		$V_{CC} = 2.7 V$		12	3	-	15	-	ns
		$V_{CC}$ = 3.0 V to 3.6 V	[3]	8	2	-	10	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V	[4]	6	1	-	8	-	ns
t <sub>h</sub>	hold time	nD to nCP; see Figure 6							
		V <sub>CC</sub> = 1.2 V		-	-10	-	-	-	ns
		$V_{CC} = 2.0 V$		3	-2	-	3	-	ns
		$V_{CC} = 2.7 V$		3	-2	-	3	-	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		3	-2	-	3	-	ns
		$V_{CC}$ = 4.5 V to 5.5 V		3	-2	-	3	-	ns
f <sub>max</sub>	maximum	nCP; see <u>Figure 6</u>							
	frequency	$V_{CC} = 2.0 V$		14	40	-	12	-	MHz
		$V_{CC} = 2.7 V$		50	90	-	40	-	MHz
		$V_{CC}$ = 3.0 V to 3.6 V	[3]	60	100	-	48	-	MHz
		$V_{CC}$ = 4.5 V to 5.5 V	<u>[4]</u>	70	110	-	56	-	MHz
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	<u>[5]</u>	-	24	-	-	-	pF

#### **Table 7. Dynamic characteristics** ... continued GND (around = 0 V): for test circuit, see Figure 8

[1] Typical values are measured at  $T_{amb}$  = 25 °C.

[2]  $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}$ .

[3] Typical value measured at V<sub>CC</sub> = 3.3 V.

[4] Typical values are measured at  $V_{CC} = 5.0$  V.

[5]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$  ( $P_D$  in  $\mu$ W), where:  $f_i =$  input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

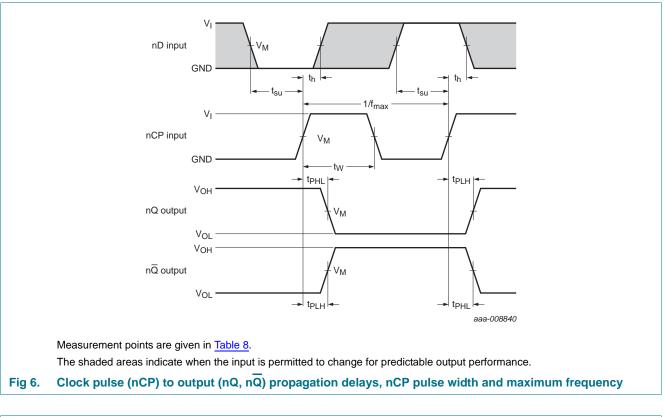
 $\Sigma (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs;

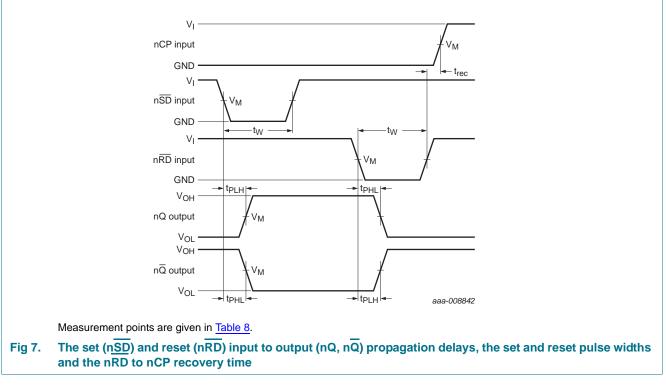
 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V.

#### Dual D-type flip-flop with set and reset; positive-edge trigger

# 11. Waveforms



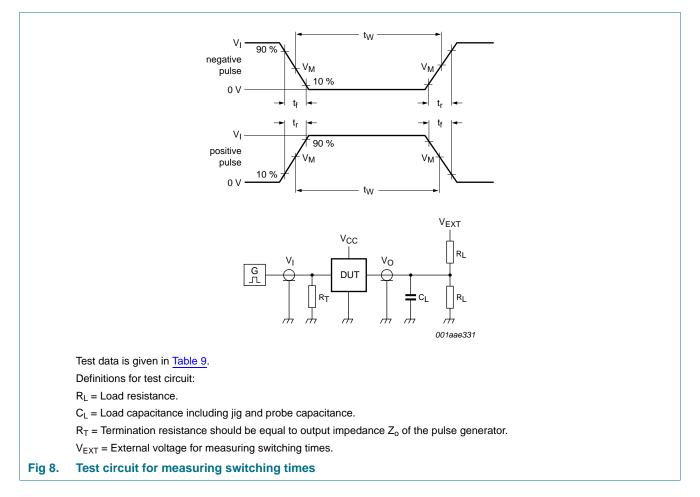


#### **NXP Semiconductors**

# 74LV74

#### Dual D-type flip-flop with set and reset; positive-edge trigger

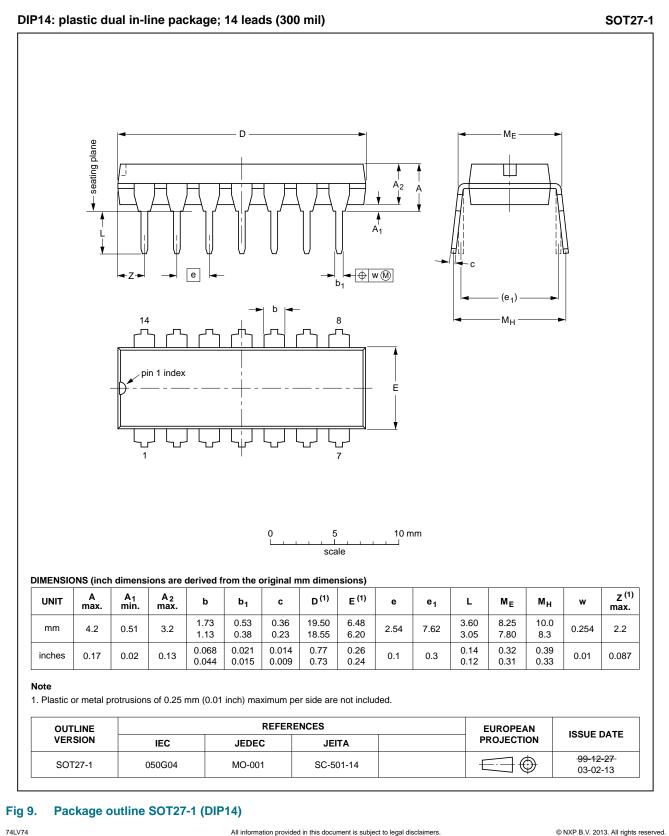
Table 8.         Measurement point	its	
Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>
< 2.7 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
2.7 V to 3.6 V	1.5 V	1.5 V
$\geq$ 4.5 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>



#### Table 9. Test data

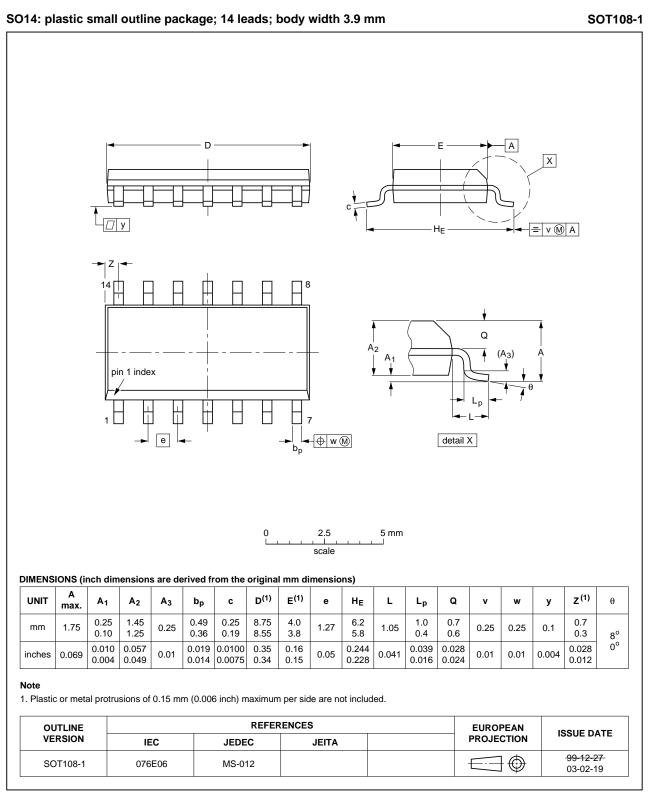
Supply voltage	Input		Load	oad		
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHL</sub> , t <sub>PLH</sub>	
< 2.7 V	V <sub>CC</sub>	2.5 ns	50 pF	1 kΩ	open	
2.7 V to 3.6 V	2.7 V	2.5 ns	50 pF, 15 pF	1 kΩ	open	
$\geq$ 4.5 V	V <sub>CC</sub>	2.5 ns	50 pF	1 kΩ	open	

# 12. Package outline



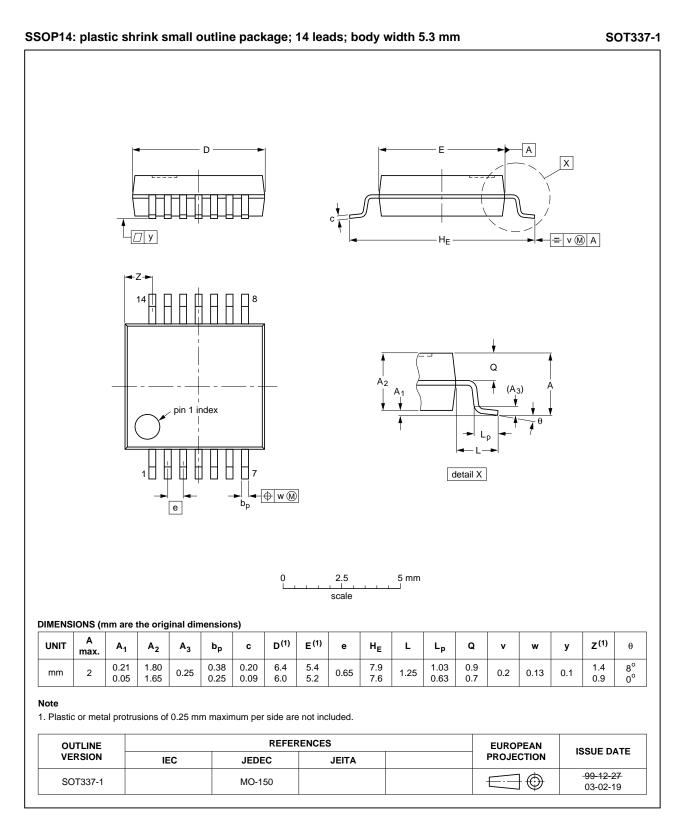
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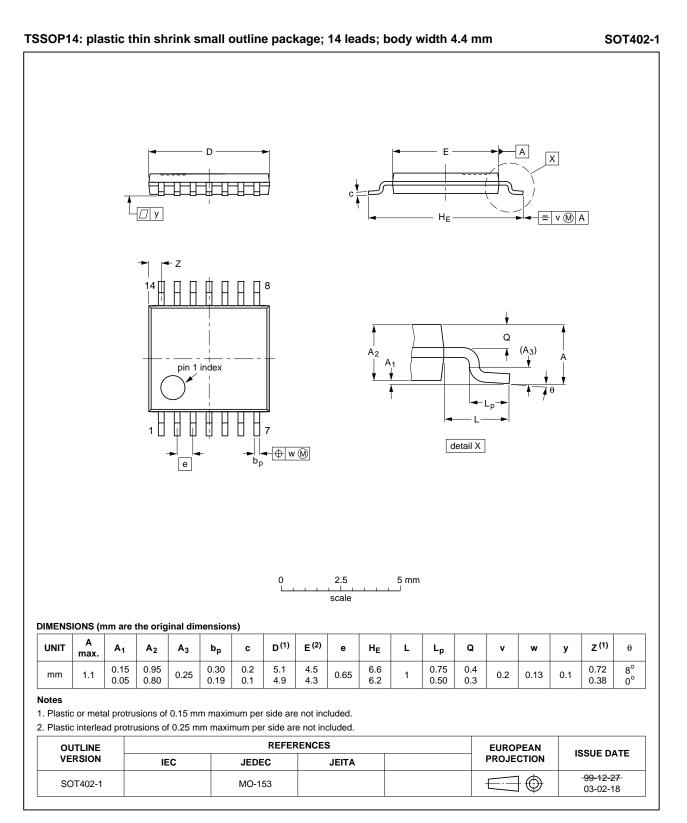
#### Fig 10. Package outline SOT108-1 (SO14)

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#### Fig 11. Package outline SOT337-1 (SSOP14)

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#### Fig 12. Package outline SOT402-1 (TSSOP14)

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# 13. Abbreviations

Table 10.	Abbreviations
Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 14. Revision history

#### Table 11. Revision history

Release date	Data sheet status	Change notice	Supersedes
20130909	Product data sheet	-	74LV74_CNV v.2
		redesigned to comply w	vith the new identity
<ul> <li>Legal texts h</li> </ul>	have been adapted to the ne	ew company name whe	ere appropriate.
<ul> <li>Family data</li> </ul>	added, see Section 9 "Stati	c characteristics"	
April 1998	Product specification	-	-
	20130909 • The format of guidelines of • Legal texts h • Family data	<ul> <li>20130909 Product data sheet</li> <li>The format of this data sheet has been guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the network of the section 9 "Static</li> </ul>	20130909       Product data sheet       -         • The format of this data sheet has been redesigned to comply we guidelines of NXP Semiconductors.       -         • Legal texts have been adapted to the new company name whete       -         • Family data added, see Section 9 "Static characteristics"

# **15. Legal information**

#### 15.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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#### **NXP Semiconductors**

# 74LV74

Dual D-type flip-flop with set and reset; positive-edge trigger

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